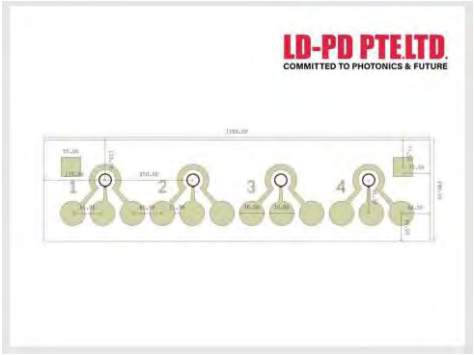
850nm 100Gb/s InGaAs 1×4 Array Photodetector Chip



Description

This product is an 850 nm 100 Gb/s InGaAs 1×4 array photodetector chip that performs photoelectric conversion. It is suitable for applications such as multimode transceivers and optical receivers.

Features

- Large photosensitive area
- Low capacitance
- Low dark current
- High responsivity

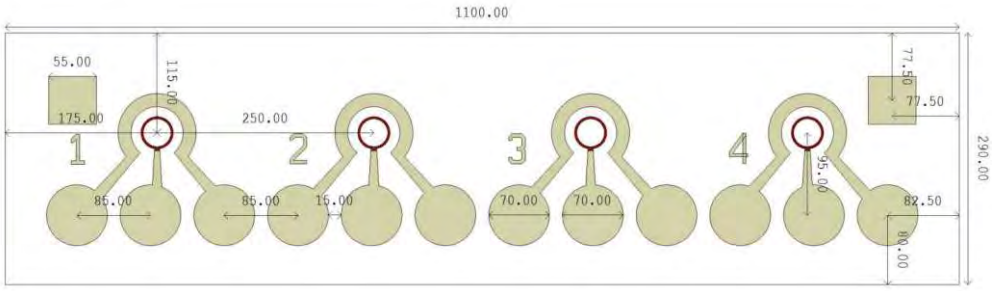
Specifications

Unless otherwise specified, measurements are taken at 25°C

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Operating Temperature	To		0		75	°C
Storage Temperature	Ts		-40		85	°C
Operating Wavelength	λ			850		nm
Bias Voltage	Vb		3		6	V
Active Area Diameter	Φ			32		μm
Responsivity	R	λ = 1550 nm, Vb = 3 V		0.6		A/W
Dark Current	Id	Vb = 3 V		0.1	1	nA
Capacitance	C	Vb= 3 V		100		fF
Series Resistance	Rs			10		Ω
3 dB Bandwidth (15 Ω TIA)	BW	Ps, o= 0 dBm, Vb = 3 V		32		GHz

62 Highland Ave., Bethlehem, PA 18017, USA
Sales: contact@cybel-llc.com | Web: www.cybel-llc.com | Tel: +1 (610) 691-7012

Dimensions and Pin definitions



Appearance	Min. Value	Typical Value	Max. Value	Unit
Length	1050	1100	1150	μm
Width	240	290	340	μm
Thickness	185	200	215	μm

Precautions for Use

- Necessary ESD protection measures should be taken to prevent the chip from electrostatic damage.
- Extreme care is required when handling the chip, and vacuum suction is recommended for chip handling.
- Parameters such as wire bonding force and temperature must be set carefully to avoid damaging the chip.